

Title (en)

COMPOSITION AND METHOD FOR REMOVING ION-IMPLANTED PHOTORESIST

Title (de)

ZUSAMMENSETZUNG UND VERFAHREN ZUR ENTFERNUNG VON IONENIMPLANTIERTEM FOTOLACK

Title (fr)

COMPOSITION ET PROCÉDÉ POUR RETIRER UN PHOTORÉSIST À IMPLANTATION IONIQUE

Publication

EP 2190967 A4 20101013 (EN)

Application

EP 08827598 A 20080820

Priority

- US 2008073650 W 20080820
- US 96545607 P 20070820

Abstract (en)

[origin: WO2009026324A2] A method and mineral acid-containing compositions for removing bulk and/or hardened photoresist material from microelectronic devices have been developed. The mineral acid-containing composition includes at least one mineral acid, at least one sulfur-containing oxidizing agent, and optionally at least one metal ion-containing catalyst. The mineral acid-containing compositions effectively remove the hardened photoresist material while not damaging the underlying silicon-containing layer(s).

IPC 8 full level

C11D 7/08 (2006.01); **C01B 32/50** (2017.01); **C11D 7/26** (2006.01); **H01L 21/02** (2006.01)

CPC (source: EP US)

G03F 7/423 (2013.01 - EP US); **H01L 21/31133** (2013.01 - EP US)

Citation (search report)

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- See references of WO 2009026324A2

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MT NL NO PL PT RO SE SI SK TR

DOCDB simple family (publication)

WO 2009026324 A2 20090226; **WO 2009026324 A3 20090514**; EP 2190967 A2 20100602; EP 2190967 A4 20101013; JP 2010541192 A 20101224; KR 20100056537 A 20100527; SG 183744 A1 20120927; TW 200927918 A 20090701; US 2011039747 A1 20110217

DOCDB simple family (application)

US 2008073650 W 20080820; EP 08827598 A 20080820; JP 2010521985 A 20080820; KR 20107006087 A 20080820; SG 2012061735 A 20080820; TW 97131792 A 20080820; US 67386008 A 20080820